NSN 5961-01-031-1999

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View Online at https://aerobasegroup.com/nsn/5961-01-031-1999 **Inclosure Material:** Metal **Overall Length:** 1.125 inches **End Application:** Control panel, culter-hammer inc **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 1.031 inches and 1.062 inches **Thread Size:** 0.500 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1000.0 repetitive peak reverse voltage and 1100.0 nonrepetitive peak reverse voltage and 1000.0 repetitive peak off-state voltage **Current Rating Per Characteristic:** 110.00 amperes forward current, total rms nanoamperes **Power Rating Per Characteristic:** 400.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Mtg hardware included; junction pattern arrangement: pnpn **Test Data Document:** 20019-21-0001 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug and 1 screw Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

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